

For Further Growth Together

# SN0620G3

## SiC Schottky Barrier Diode

#### **Features**

- Silicon Carbide Schottky Barrier Diode
- Small die size
- Low IR
- High-Recovery Speed

### **Applications**

- Switch mode power supplies
- Power Factor Correction
- Secondary Side Rectification
- PV Power Conditioners

#### Maximim Ratings (Ta=25°C) (in case of TO-220 PKG)

Parameter	Symbol	Conditions	Limit	Unit
Repetitive peak reverse voltage	Vrm		650	V
Reverse voltage (DC)	VR		650	V
Forward current (DC)	lF		20	Α
Surge no repetitive forward current	Ifsм	10ms Sinusoidal	100	Α
Junction temperature	Tj		175	°C
Storage temperature	Tstg		-55 to +175	°C

### Electrical Characteristics (Ta=25°C) (in case of TO-220 PKG)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
DC blocking voltage	VDC	In=100uA	650	-	-	V
Forward voltage	VF	I⊧=20A, Ta=25℃	-	1.47	1.91	V
		I⊧=20A, Ta=150°C	-	1.91	-	V
		I⊧=20A, Ta=175°C	-	2.06	-	V
Reverse current	lr	VR=650V, Ta=25℃	-	0.4	400	uA
		VR=650V, Ta=150°C	-	5	-	uA
		VR=650V, Ta=175°C	-	11	-	uA
Total capacitance	С	V <sub>R</sub> =1V, f=1MHz	-	514	-	pF
Total capacitive charge	Qc	V <sub>R</sub> =400V, di/dt=350A/us	-	47	-	nC
Switching time	tc	V <sub>R</sub> =400V, di/dt=350A/us	-	25	-	nS

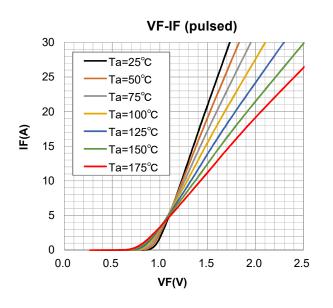


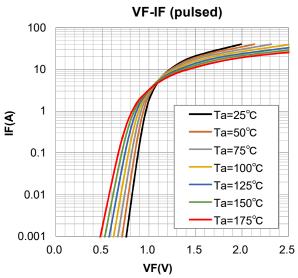


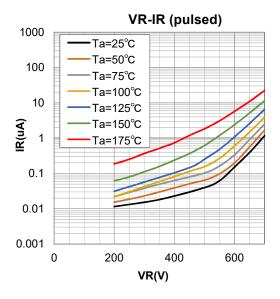
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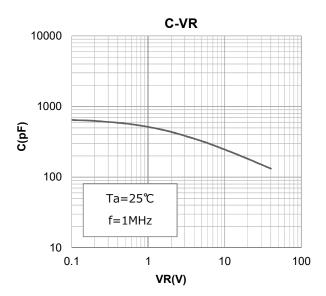
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Electrical Characteristics curves (in case of TO-220 PKG)











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#### NOTE

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- 2) Please request for the specification sheet before use.
- 3) Since the products are in wafer form, the values in this document are for reference only.
- 4) Although we strive to improve the quality of our products, they may malfunction or fail. When using this product, please implement a safety design suitable for the system within your responsibility.
- 5) Although this document has been prepared with great care, we assume no responsibility for any damages incurred due to errors in the provoded information.
- 6) If the operating environment (e.g., high temperature, high voltage, high current) is severe, the reverse current may become excessively large and the device may be destroyed due to the increased reverse
- 7) The absolute maximum ratings must not be exceeded even momentarily. Do not exceed the absolute maximum ratings for any of the multiple ratings.
- 8) In particular, when evaluating or using the product in a resin-encapsulated package or in a sealed environment, be sure to measure the temperature and confirm that the maximum junction temperature designated as the maximum ratings is not exceeded.
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